



PATENT 1765C82
ATTY. DOCKET NO.: P66182US0

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Young-Hee MUN

Group Art Unit: 1765

Serial No.: 09/742,127

Examiner: M. Song

Filed: December 22, 2000

For: METHOD FOR TREATING A SEMICONDUCTOR WAFER THERMALLY
AND SEMICONDUCTOR WAFER FABRICATED BY THE SAME

TRANSMITTAL

Assistant Commissioner of Patents
Washington, D.C. 20231

RECEIVED
MAR 05 2003
GROUP 1700

Sir:

Transmitted herewith is an Amendment Under Rule 1.111 for filing in the above-captioned patent application.

The fee has been calculated as shown below:

	Claims Remaining After Amendment		Highest Number Previously Paid For	Present Extra	Small Entity Rate Addit. Fee	(or)	Other Than A Small Entity Rate Addit. Fee
Total	23	-	20 =	3	x 09 = \$		x 18 = \$ 54.00
Indep.	07	-	05 =	2	x 42 = \$		x 84 = \$168.00
First Presentation of Multiple Dependent Claims					+130 = \$		+ 260 = \$
Total Additional Fee					\$		\$222.00

XXXX A check in the amount of \$ 222.00 is attached for: Additional Claim Fees

XXXX If a Petition for Extension of Time is necessary and the Petition and/or the check is not enclosed, this will act as the Petition and applicant herewith petitions the Commissioner to extend the time for response and charge any fees necessary under 37 CFR 1.17 (a)(1)-(5) to Deposit Account No. 06-1358. The Commissioner is also authorized to charge payment of any other additional fees associated with this communication or credit any overpayment to Deposit Account No. 06-1358. A duplicate copy of this sheet is attached.

Respectfully submitted,
JACOBSON HOLMAN PLLC

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Atty. Docket: 12597/P66182US0
Telephone: (202)638-6666
Date: February 26, 2003
YSH:SCB
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AMENDMENT UNDER RULE 1.111

Assistant Commissioner
of Patents
Washington, D.C. 20231

February 26, 2003

Sir:

In response to the Office Action (Paper No. 9) dated November 26, 2002, kindly
amend the above-identified patent application as follows:

IN THE CLAIMS

Please cancel claim 18 without prejudice or disclaimer and amend claims 1, 3, 4,
8 and 17 to read as follows:

1. (Twice Amended) A method of treating a wafer thermally to remove defects contained in
single crystalline semiconductor, the method comprising the steps of:

B1 carrying out a heat treatment on the wafer at a temperature equal to or higher than
1200 °C under a non-oxidative atmosphere containing hydrogen; and
carrying out a rapid thermal annealing on the wafer at a temperature equal to or
lower than 800°C for a period having a duration of two minutes or less.

02/28/2003 MBELETE1 00000039 09742127

01 FC:1201
02 FC:1202

168.00 DP
54.00 DP